

MOSFET

OptiMOS™ 6 Power-Transistor, 60 V

Features

- Optimized for low voltage drives and battery powered applications
- Optimized for high performance SMPS
- N-channel, normal level
- Very low on-resistance $R_{DS(on)}$
- Superior thermal resistance
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC JESD47, JESD22 and J-STD-020.

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(on),max}$	0.9	mΩ
I_D	344	A
Q_{oss}	137	nC
Q_G	97	nC
Q_{rr} (1000A/μs)	265	nC

Part number	Package	Marking	Related links
ISC009N06NM6	PG-TDSON-8	009N06N6	-

PG-TDSON-8

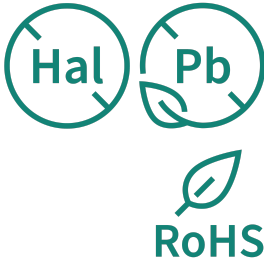
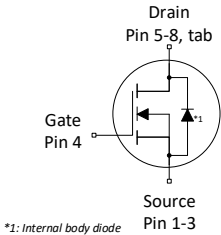
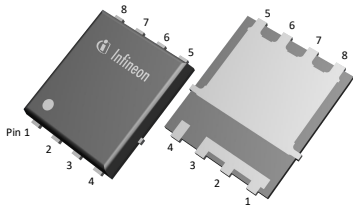




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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	344	A	$V_{GS}=10\text{ V}, T_C=25\text{ °C}$
				243		$V_{GS}=10\text{ V}, T_C=100\text{ °C}$
				220		$V_{GS}=8\text{ V}, T_C=100\text{ °C}$
				40		$V_{GS}=10\text{ V}, T_A=25\text{ °C}, R_{thJA}=50\text{ °C/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	1376	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	579	mJ	$I_D=50\text{ A}, R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	221	W	$T_C=25\text{ °C}$
				3.0		$T_A=25\text{ °C}, R_{thJA}=50\text{ °C/W}^{2)}$
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.34	0.68	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}		-	20		
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}		-	50		

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.1	2.7	3.3	V	$V_{DS}=V_{GS}$, $I_D=118\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1	1.0	μA	$V_{DS}=48\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$
			10	100		$V_{DS}=48\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.74	0.9	m Ω	$V_{GS}=10\text{ V}$, $I_D=50\text{ A}$
Drain-source on-state resistance ⁶⁾	$R_{DS(on)}$	-	0.82	1.1	m Ω	$V_{GS}=8\text{ V}$, $I_D=25\text{ A}$
Gate resistance	R_G	-	0.84	-	Ω	-
Transconductance ⁶⁾	g_{fs}	110	220	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=50\text{ A}$

⁶⁾ Defined by design. Not subject to production test.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance ⁷⁾	C_{iss}	-	6400	8300	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁷⁾	C_{oss}		2200	2900		
Reverse transfer capacitance ⁷⁾	C_{rss}		72	130		
Turn-on delay time	$t_{d(on)}$	-	13.5	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r		6.0			
Turn-off delay time	$t_{d(off)}$		32.9			
Fall time	t_f		8.5			

⁷⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁸⁾

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	28	-	nC	$V_{DD}=30\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$		17.3	-	nC	
Gate to drain charge ⁹⁾	Q_{gd}		20	30	nC	
Switching charge	Q_{sw}		31	-	nC	
Gate charge total ⁹⁾	Q_g		97	121	nC	
Gate plateau voltage	$V_{plateau}$		4.3	-	V	
Output charge ⁹⁾	Q_{oss}	-	137	182	nC	$V_{DS}=30\text{ V}$, $V_{GS}=0\text{ V}$

⁸⁾ See "Gate charge waveforms" for parameter definition

⁹⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	201	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$			1376		
Diode forward voltage	V_{SD}	-	0.79	1.0	V	$V_{GS}=0\text{ V}$, $I_F=50\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ¹⁰⁾	t_{rr}	-	51	102	ns	$V_R=30\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁰⁾	Q_{rr}		66	132	nC	
Reverse recovery time ¹⁰⁾	t_{rr}	-	29	58	ns	$V_R=30\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁰⁾	Q_{rr}		265	530	nC	

¹⁰⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

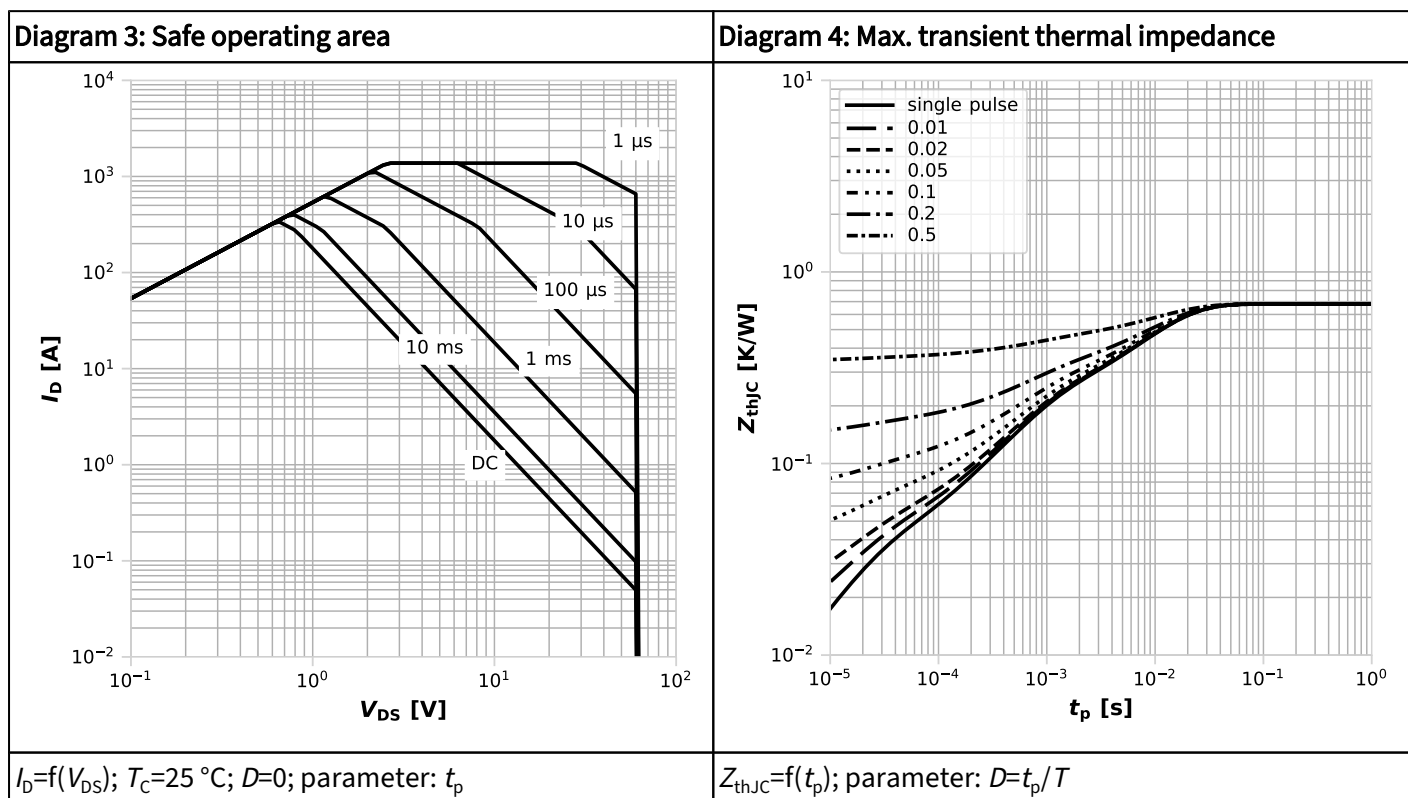
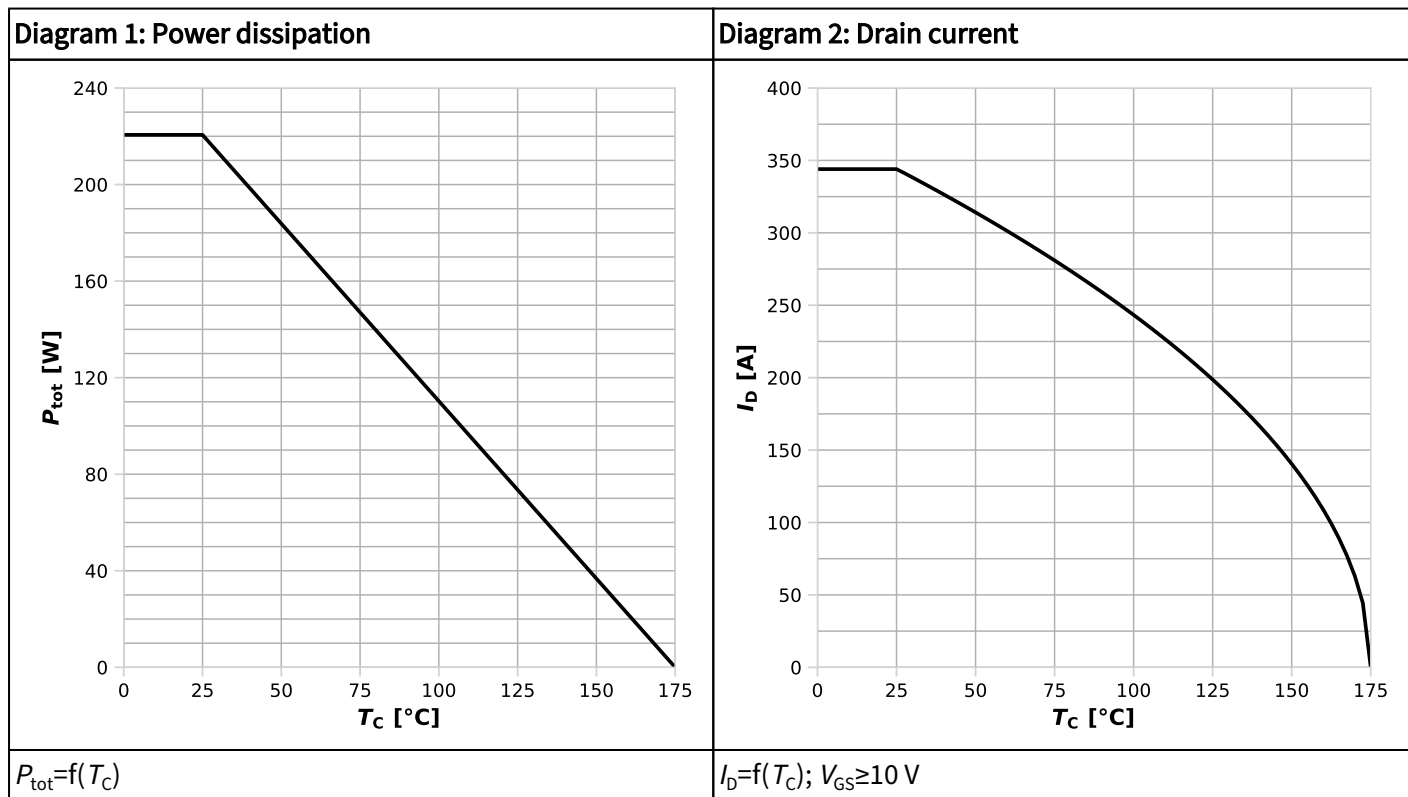
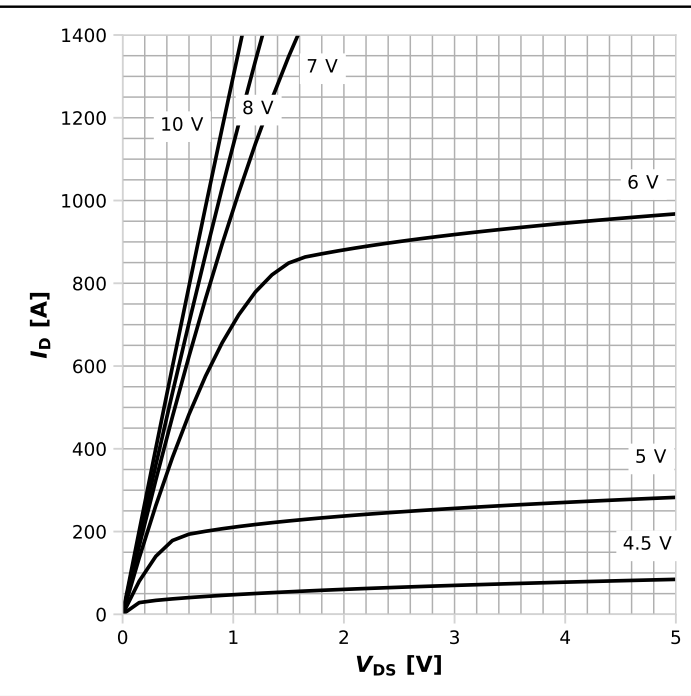
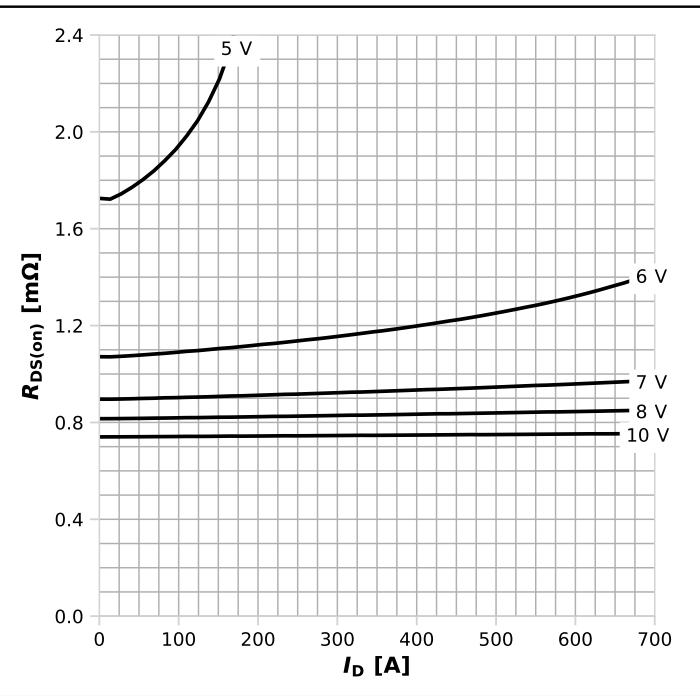


Diagram 5: Typ. output characteristics



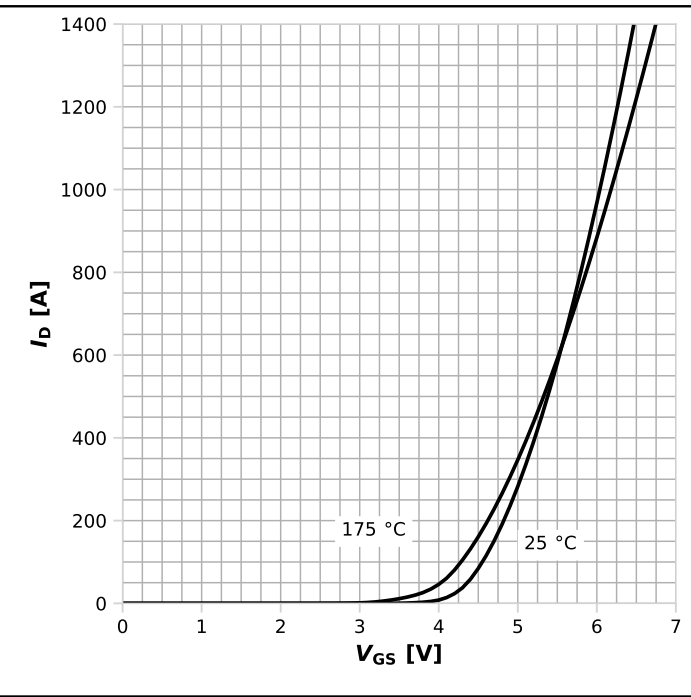
$I_D=f(V_{DS})$, $T_j=25\text{ }^{\circ}\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



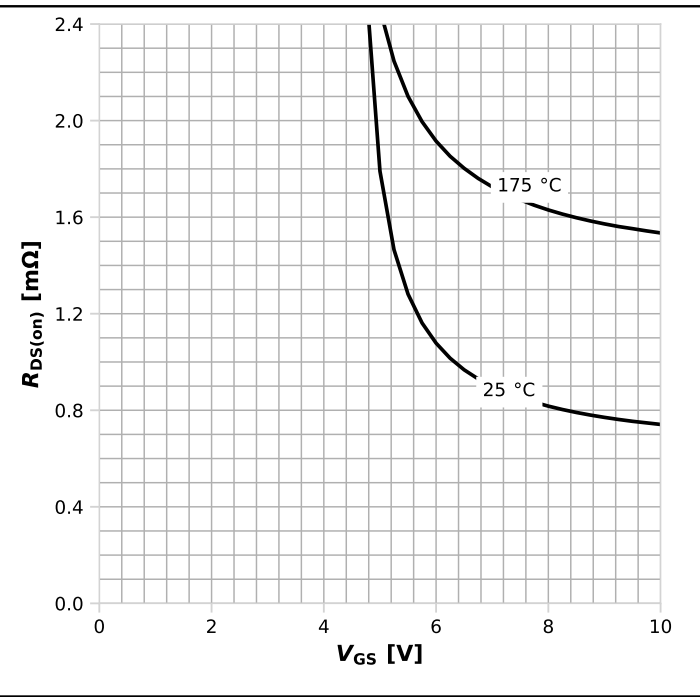
$R_{DS(on)}=f(I_D)$, $T_j=25\text{ }^{\circ}\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



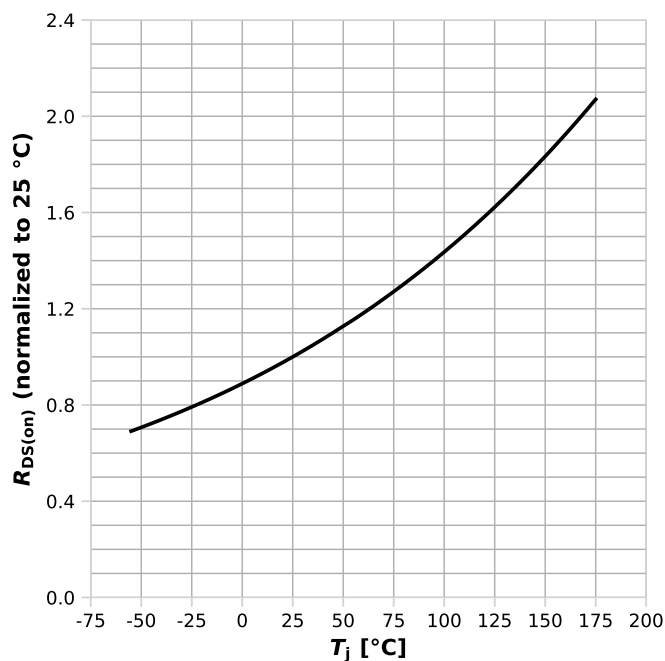
$I_D=f(V_{GS})$, $|V_{DS}|>2|I_D|R_{DS(on)\text{max}}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



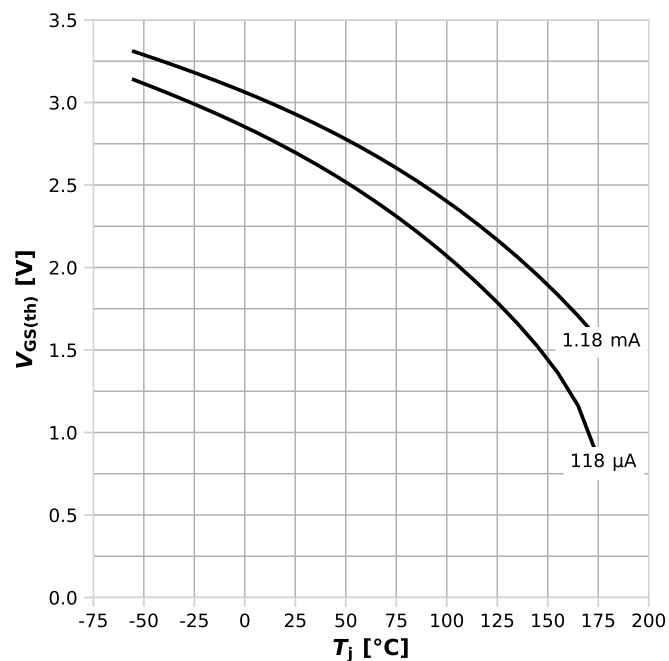
$R_{DS(on)}=f(V_{GS})$, $I_D=50\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



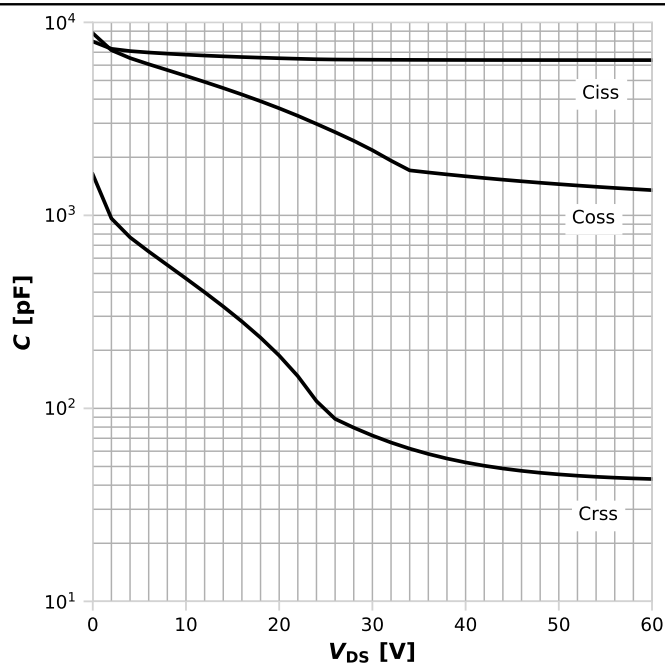
$$R_{DS(on)} = f(T_j), I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



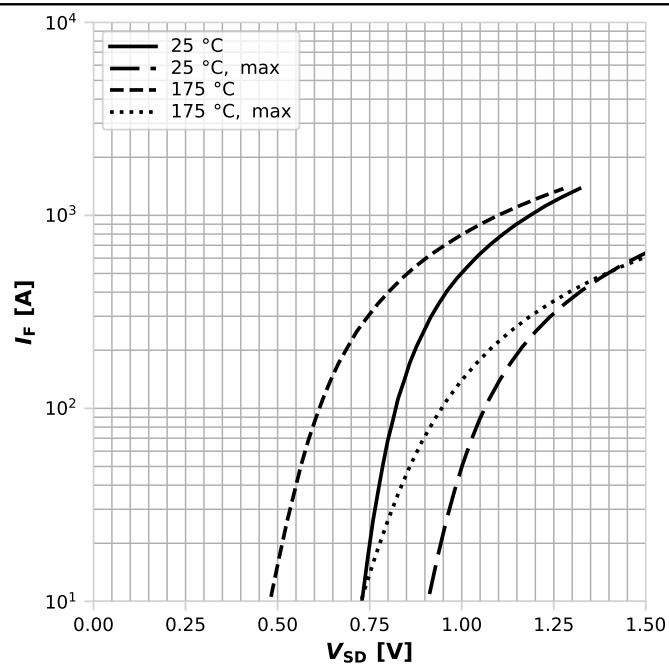
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances



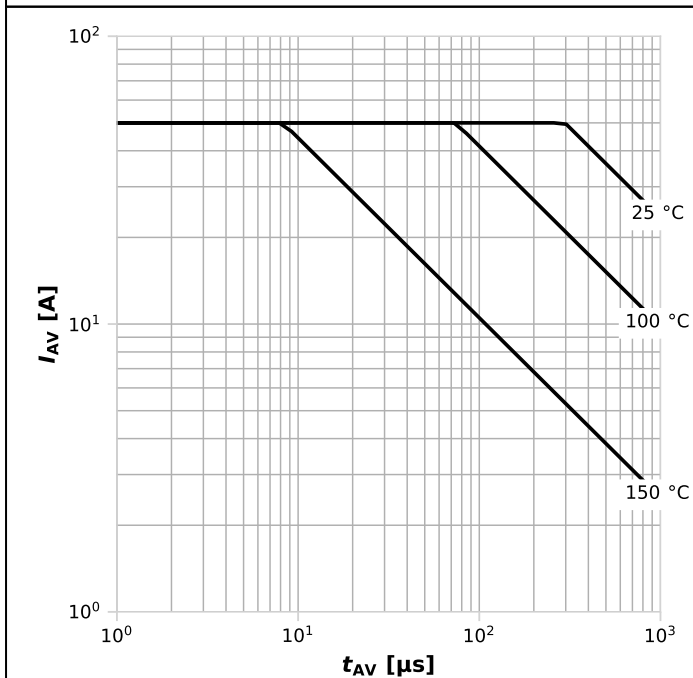
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



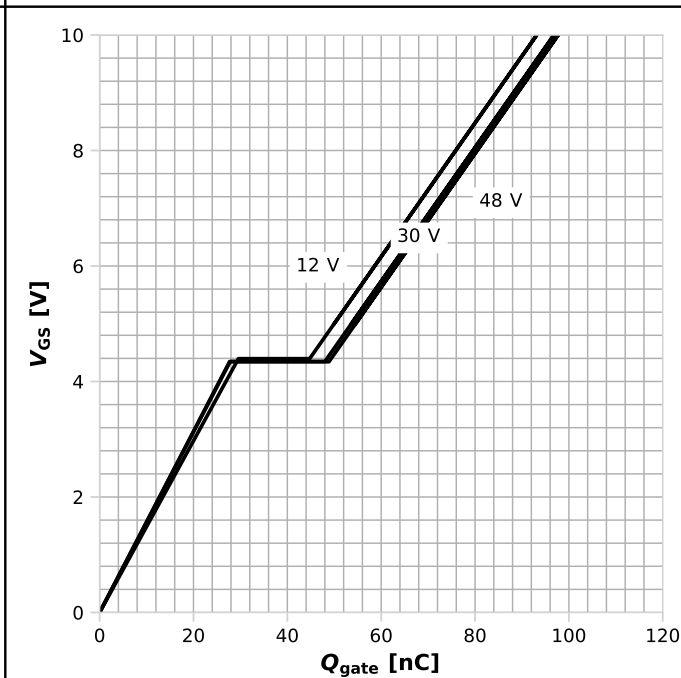
$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

Diagram 13: Avalanche characteristics



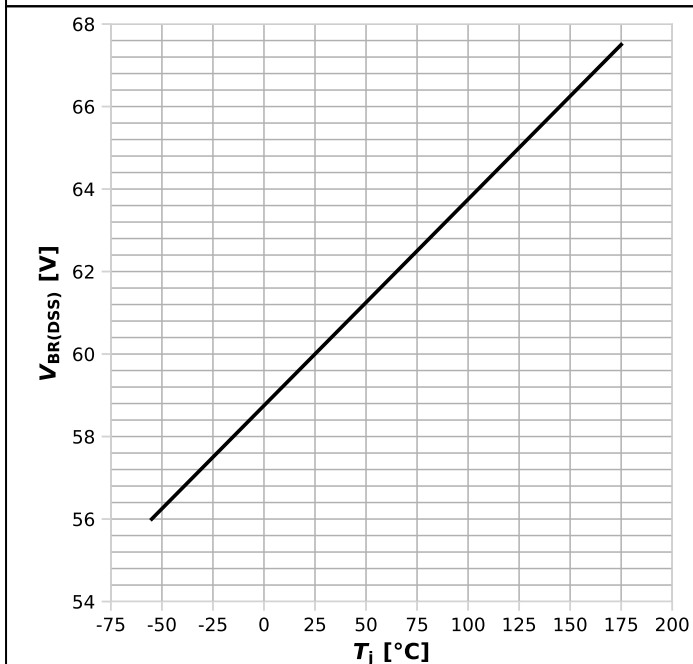
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



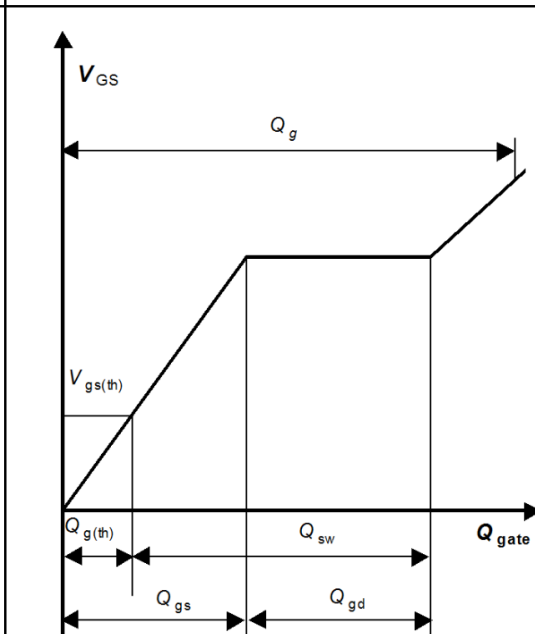
$V_{GS}=f(Q_{gate})$, $I_D=50\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; $I_D=10\text{ mA}$

Gate charge waveforms



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5 Package outlines

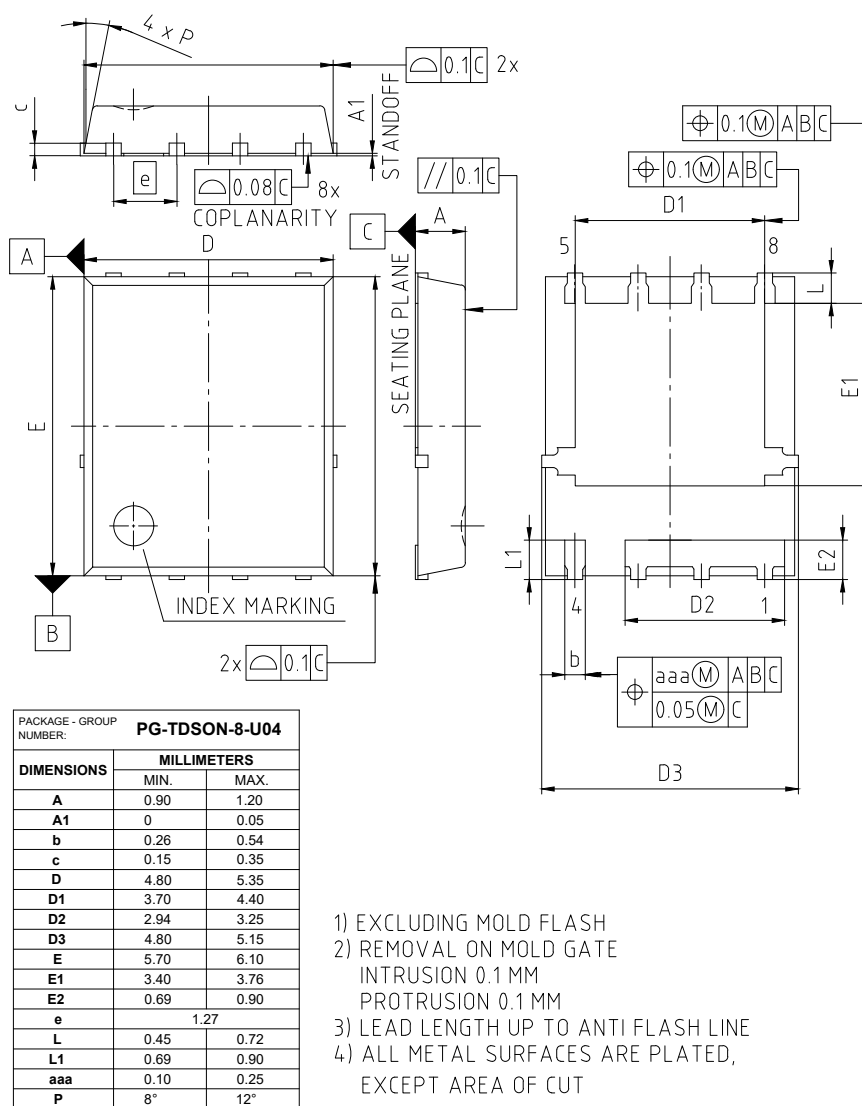


Figure 1 Outline PG-TDSON-8, dimensions in mm

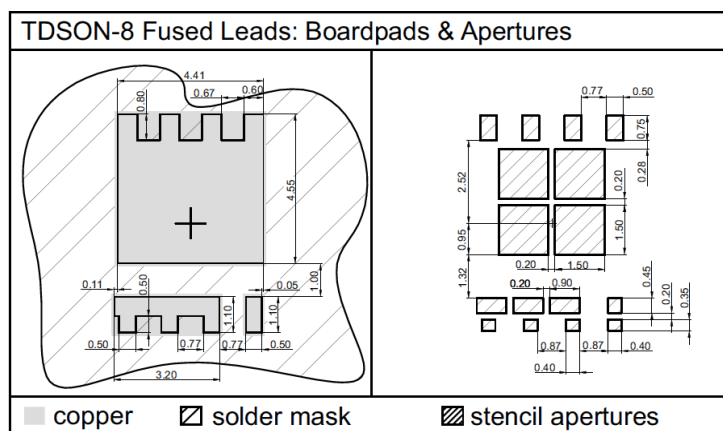


Figure 2 Footprint drawing PG-TDSON-8, dimensions in mm

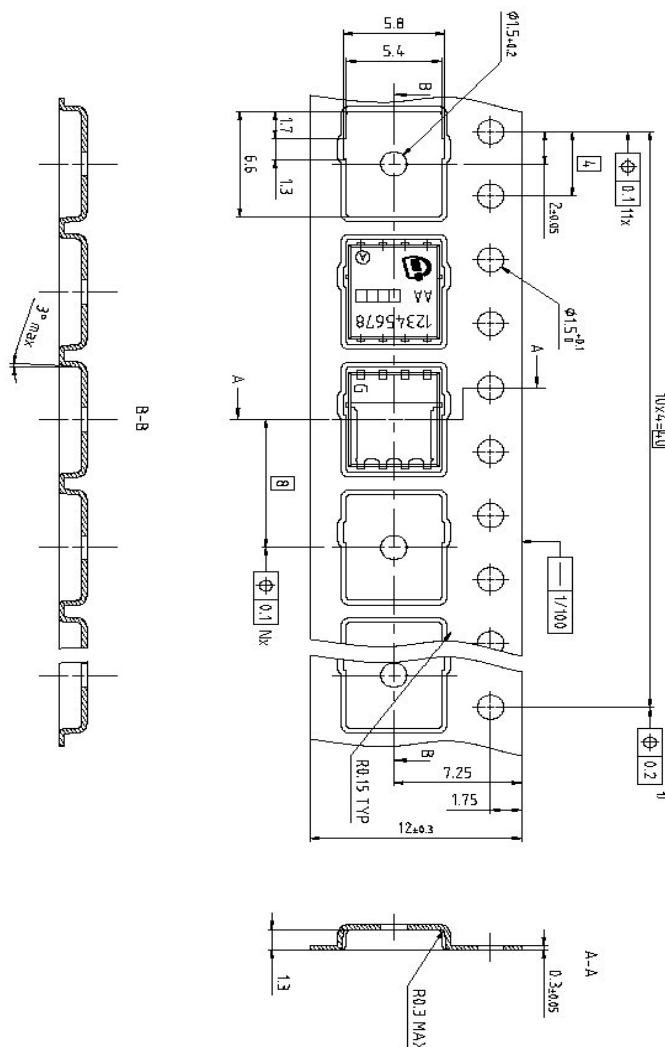


Figure 3 Packaging variant PG-TDSON-8, dimensions in mm

Revision history

ISC009N06NM6

Revision 2025-07-07, Rev. 2.1

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2024-05-08	Release of final
2.1	2025-07-07	Revised Rdson at Vgs from 6V to 8V

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